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**(54) POLISHING METHOD FOR SILICON WAFER OF
SEMICONDUCTOR**

(57) Abstract:

PURPOSE: To reduce the OSF density, enhance the surface precision, and enhance the producibility in a polishing method for the initial stage of mechanical polishing in the manufacturing processes for semiconductor silicon wafers.

CONSTITUTION: The polishing rate is enhanced using a polishing pressure for example 10-50% higher than the

conventional level, i.e., between 0.55 and 0.8kg/cm², and the secular change of a polishing cloth resulting from polishing in the high pressure region is corrected by co-rubbing using a diamond dresser, and as a final stage, a surface treatment is made with a polishing pressure for example 10-50% sunk from the conventional level, i.e., ranging between 0.25 and 0.45kg/cm², and thereby the OSF density is reduced and the surface precision is enhanced.

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